

600 - 650 V MDmeshTM DM6

fast-recovery SJ MOSFETs boost efficiency and robustness



MDmeshTM DM6 fast-recovery body diode technology improves efficiency and system reliability thanks to new lifetime killing process

Combining an optimized capacitance profile and lifetime killing process that results in a low gate charge (Q_g), very low recovery charge (Q_r), low recovery time (t_{rr}) and an excellent improvement in $R_{DS(on)}$ per area, the MDmeshTM DM6 MOSFET series is today's reference for full- and half-bridge topologies.

Thanks to our new MDmesh™ DM6 series, power electronic designers are now ready for new scenarios targeting higher efficiency and very impressive power density for super robust power conversion topologies.

KEY FEATURES

- Extremely low R_{DS(on)}*area and Q_g and optimized capacitance profile for light load conditions
- 600 650 V BVdss rated
- Extremely high dv/dt
- Optimized body diode recovery phase
- Optimized softness

KEY BENEFITS

- Extremely high efficiency performance and increased power density
- More robust power conversion in ZVS, full and half bridge topologies
- Higher operation frequencies and better thermal management

KEY APPLICATIONS

- Charging stations for electric vehicles
- LED lighting
- Telecom
- Servers
- Solar inverters
- Reduced EMI

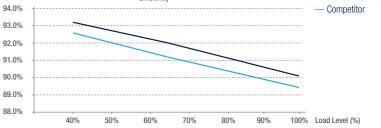
MDmesh™ DM6 SERIES

600 - 650 V BVdss rated

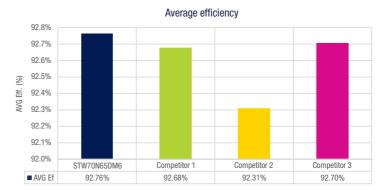
ST's latest fast-recovery body diode super-junction MOSFET technology is optimized for ZVS, full- and halfbridge topologies. With a breakdown voltage of 600 V, MDmesh™ DM6 power MOSFETs are available in a wide range of package options including a TO-Leadless (TO-LL) package solution, allowing efficient thermal management.

η (%) _ STW65N60DM6 - Competitor

Efficiency test performed on 2 kW ZVS topology







AVAILABLE POWER TRANSISTORS IN OUR HIGH-VOLTAGE, SUPER-JUNCTION 600 - 650 V MDmesh™ DM6 SERIES

MDmesh™ DM6 Product Plan											
R _{DS(on)} (Ω)	ld max (A)	Qg (nC)	trr (ns)	D ² PAK	PowerFLAT	TO 000	T0-220FP	T0-247			TOLL
					8x8 HV	T0-220		Standard	Long Lead	Kelvin Pin	T0-LL
0.240 0.255**	15	18	85	STB22N60DM6	STL22N60DM6	STP22N60DM6	STF22N60DM6				
0.195 0.210**	18	23	92		STL26N60DM6	STP26N60DM6	STF26N60DM6				
0.128 0.140**	25	35	100	STB33N60DM6	STL33N60DM6	STP33N60DM6	STF33N60DM6				
0.095 0.100**	30	44	105		STL45N60DM6	STP45N60DM6		STW45N60DM6			
0.071	38	61	115					STW65N60DM6	STWA65N60DM6		ST065N60DM6*
0.054	48	80	124						STWA67N60DM6*		ST067N60DM6*
0.042	62	106	138					STW70N60DM6	STWA70N60DM6	STW70N60DM6-4	
0.036	72	117	140					STW75N60DM6	STWA75N60DM6		
0.091	33	54	118	STB50N65DM6		STP50N65DM6		STW50N65DM6			
0.059	48	80	128					STW68N65DM6*	STWA68N65DM6*		
0.039	68	115	160					STW70N65DM6	STWA70N65DM6		_

Note: * In development

** Refered to PowerFLATTM







To explore the complete MDmeshTM DM6 product portfolio, visit www.st.com or use our ST-MOSFET-Finder mobile app for Android and iOS.



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